



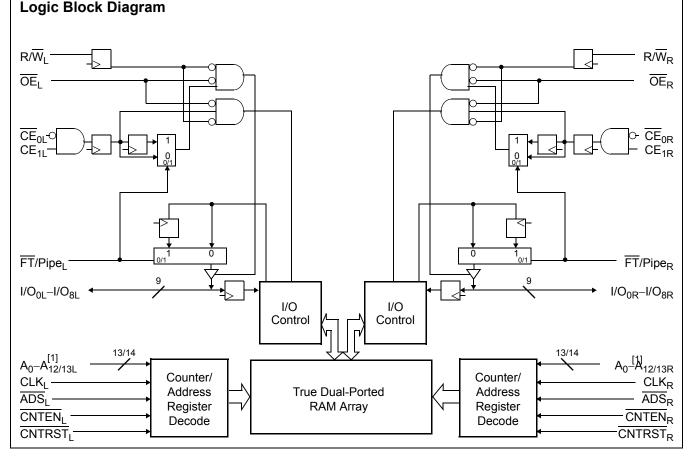
# CY7C09159AV CY7C09169AV

# 3.3V 8K/16K x 9 Synchronous Dual Port Static RAM

### Features

- True Dual-Ported memory cells which allow simultaneous access of the same memory location
- Two Flow-Through/Pipelined devices
  - 8K x 9 organization (CY7C09159AV)
  - 16K x 9 organization (CY7C09169AV)
- Three Modes
  - Flow-Through
  - Pipelined
  - Burst
- Pipelined output mode on both ports allows fast 83-MHz operation
- 0.35-micron CMOS for optimum speed/power
- High-speed clock to data access 9 and 12 ns (max.)

- 3.3V Low operating power
  - Active = 135 mA (typical)
  - Standby = 10  $\mu$ A (typical)
- Fully synchronous interface for easier operation
- · Burst counters increment addresses internally
  - Shorten cycle times
  - Minimize bus noise
  - Supported in Flow-Through and Pipelined modes
- Dual Chip Enables for easy depth expansion
- Automatic power-down
- Commercial and industrial temperature ranges
- Available in 100-pin TQFP
- Pb-Free packages available



Notes:

1.  $A_0 - A_{12}$  for 8K;  $A_0 - A_{13}$  for 16K.

**Cypress Semiconductor Corporation** Document #: 38-06053 Rev. \*B 198 Champion Court • San Jose, CA 95134-1709 • 408-943-2600 Revised September 6, 2005



## **Functional Description**

The CY7C09159AV and CY7C09169AV are high-speed synchronous CMOS 8K and 16K x 9 dual-port static RAMs. Two ports are provided, permitting independent, simultaneous access for reads and writes to any location in memory.<sup>[2]</sup> Registers on control, address, and data lines allow for minimal set-up and hold times. In pipelined output mode, data is registered for decreased cycle time. Clock to data valid  $t_{CD2} = 9$  ns (pipelined). Flow-through mode can also be used to bypass the pipelined output register to eliminate access latency. In flow-through mode data will be available  $t_{CD1} = 18$  ns after the address is clocked into the device. Pipelined output or flow-through mode is selected via the FT/Pipe pin.

Each port contains a burst counter on the input address register. The internal write pulse width is independent of the LOW- to-HIGH transition of the clock signal. The internal write pulse is self-timed to allow the shortest possible cycle times.

A HIGH on  $\overline{CE}_0$  or LOW on  $CE_1$  for one clock cycle will power down the internal circuitry to reduce the static power consumption. The use of multiple Chip Enables allows easier banking of multiple chips for depth expansion configurations. In the pipelined mode, one cycle is required with  $\overline{CE}_0$  LOW and  $CE_1$  HIGH to reactivate the outputs.

Counter enable inputs are provided to stall the operation of the address input and utilize the internal address generated by the internal counter for fast interleaved memory applications. A port's burst counter is loaded with the port's Address Strobe (ADS). When the port's Count Enable (CNTEN) is asserted, the address counter will increment on each LOW-to-HIGH transition of that port's clock signal. This will read/write one word from/into each successive address location until CNTEN is deasserted. The counter can address the entire memory array and will loop back to the start. Counter Reset (CNTRST) is used to reset the burst counter.

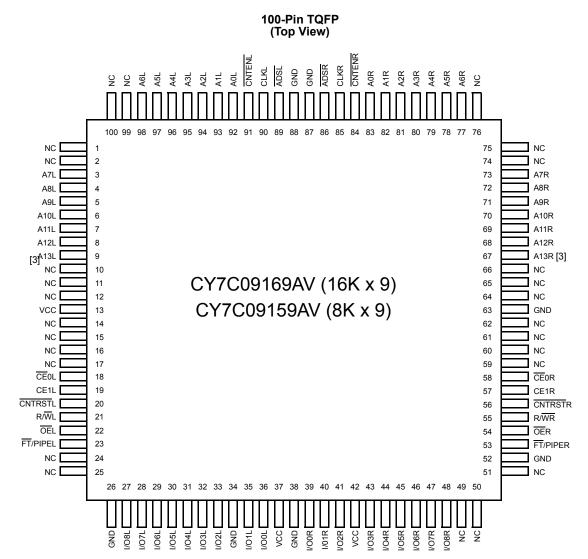
All parts are available in 100-pin Thin Quad Plastic Flatpack (TQFP) packages.

#### Note:

2. When simultaneously writing to the same location, final value cannot be guaranteed.



**Pin Configuration** 



#### **Selection Guide**

	CY7C09159AV CY7C09169AV -9	CY7C09159AV CY7C09169AV -12	Unit
f <sub>MAX2</sub> (Pipelined)	67	50	MHz
Max Access Time (Clock to Data, Pipelined)	9	12	ns
Typical Operating Current I <sub>CC</sub>	135	115	mA
Typical Standby Current for I <sub>SB1</sub> (Both Ports TTL Level)	20	20	mA
Typical Standby Current for I <sub>SB3</sub> (Both Ports CMOS Level)	10	10	μΑ

Note:

3. This pin is NC for CY7C09159AV.



## **Pin Definitions**

Left Port	Right Port	Description
A <sub>0L</sub> -A <sub>13L</sub>	A <sub>0R</sub> -A <sub>13R</sub>	Address Inputs ( $A_0-A_{12}$ for 8K; $A_0-A_{13}$ for 16K devices).
ADSL	ADS <sub>R</sub>	Address Strobe Input. Used as an address qualifier. This signal should be asserted LOW during normal read or write transactions. Asserting this signal LOW also loads the burst address counter with data present on the I/O pins.
CE <sub>0L</sub> ,CE <sub>1L</sub>	CE <sub>0R</sub> ,CE <sub>1R</sub>	Chip Enable Input. To select either the left or right port, both $\overline{CE}_0$ AND $CE_1$ must be asserted to their active states ( $\overline{CE}_0 \leq V_{IL}$ and $CE_1 \geq V_{IH}$ ).
CLKL	CLK <sub>R</sub>	Clock Signal. This input can be free-running or strobed. Maximum clock input rate is f <sub>MAX</sub> .
CNTENL	CNTENR	Counter Enable Input. Asserting this signal <u>LOW increments the burst</u> ad <u>dress counter</u> of its respective port on each rising edge of CLK. CNTEN is disabled if ADS or CNTRST are asserted LOW.
CNTRST	CNTRSTR	Counter Reset Input. Asserting this signal LOW resets the burst address counter of its respective port to zero. CNTRST is not disabled by asserting ADS or CNTEN.
I/O <sub>0L</sub> -I/O <sub>8L</sub>	I/O <sub>0R</sub> -I/O <sub>8R</sub>	Data Bus Input/Output (I/O <sub>0</sub> –I/O <sub>7</sub> for x8 devices; I/O <sub>0</sub> –I/O <sub>8</sub> for x9 devices).
OEL	OE <sub>R</sub>	Output Enable Input. This signal must be asserted LOW to enable the I/O data pins during read operations.
R/WL	R/W <sub>R</sub>	Read/Write Enable Input. This signal is asserted LOW to write to the dual-port memory array. For read operations, assert this pin HIGH.
FT/PIPE <sub>L</sub>	FT/PIPE <sub>R</sub>	Flow-Through/Pipelined Select Input. For flow-through mode operation, assert this pin LOW. For pipelined mode operation, assert this pin HIGH.
GND	•	Ground Input.
NC		No Connect.
V <sub>CC</sub>		Power Input.

## Maximum Ratings<sup>[4]</sup>

(Above which the useful life may be impaired. For user guide-lines, not tested.)
Storage Temperature –65°C to +150°C
Ambient Temperature with Power Applied55°C to +125°C
Supply Voltage to Ground Potential0.5V to +4.6V
DC Voltage Applied to Outputs in High Z State0.5V to V_{CC}+0.5V
DC Input Voltage0.5V to V <sub>CC</sub> +0.5V

Output Current into Outputs (LOW)	20 mA
Static Discharge Voltage	.>2001V
Latch-Up Current	>200 mA

# **Operating Range**

Range	Ambient Temperature	v <sub>cc</sub>
Commercial	0°C to +70°C	3.3V ± 300 mV
Industrial <sup>[5]</sup>	–40°C to +85°C	3.3V ± 300 mV

Note:4. The voltage on any input or I/O pin can not exceed the power pin during power-up5. Industrial parts are available in CY7C09169AV only.



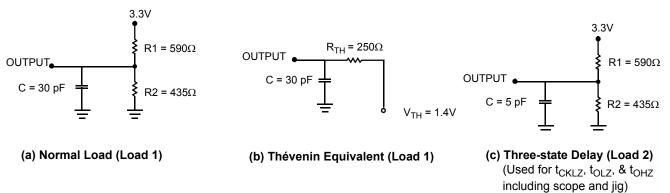
#### Electrical Characteristics Over the Operating Range

			CY7C09159AV CY7C09169AV						
				-9			-12		
Parameter	Description		Min.	Тур.	Max.	Min.	Тур.	Max.	Unit
V <sub>OH</sub>	Output HIGH Voltage (V <sub>CC</sub> = Min., I <sub>OH</sub> = -4.0 m	A)	2.4			2.4			V
V <sub>OL</sub>	Output LOW Voltage (V <sub>CC</sub> = Min., I <sub>OH</sub> = +4.0 m	A)			0.4			0.4	V
V <sub>IH</sub>	Input HIGH Voltage		2.0			2.0			V
V <sub>IL</sub>	Input LOW Voltage			0.8			0.8	V	
I <sub>OZ</sub>	Output Leakage Current		-10		10	-10		10	μA
I <sub>CC</sub>	Operating Current (V <sub>CC</sub> = Max.,	Com'l.		135	230		115	180	mA
	I <sub>OUT</sub> = 0 mA) Outputs Disabled	Ind. <sup>[5]</sup>					155	250	mA
I <sub>SB1</sub>	Standby Current (Both Ports TTL Level) <sup>[6]</sup>	Com'l.		20	75		20	70	mA
	$CE_L \& CE_R \ge V_{IH}, f = f_{MAX}$	Ind. <sup>[5]</sup>					30	80	mA
I <sub>SB2</sub>	Standby Current (One Port TTL Level) <sup>[6]</sup>	Com'l.		95	155		85	140	mA
	$CE_L \mid CE_R \ge V_{IH}, f = f_{MAX}$	Ind. <sup>[5]</sup>					95	150	mA
I <sub>SB3</sub>	Standby Current (Both Ports CMOS Level) <sup>[6]</sup>	Com'l.		10	500		10	500	μA
	$CE_{L} \& CE_{R} \ge V_{CC} - 0.2V, f = 0$	Ind. <sup>[5]</sup>					10	500	μA
I <sub>SB4</sub>	Standby Current (One Port CMOS Level) <sup>[6]</sup>	Com'l.		85	115	1	75	100	mA
	$CE_L \mid CE_R \ge V_{IH}, f = f_{MAX}$	Ind. <sup>[5]</sup>	1		·		85	110	mA

#### Capacitance

Parameter	Description	Test Conditions	Max.	Unit
C <sub>IN</sub>	Input Capacitance			pF
C <sub>OUT</sub>	Output Capacitance	$V_{\rm CC} = 3.3 V$	10	pF

#### **AC Test Loads**



Note: 6.  $\overline{CE}_L$  and  $\overline{CE}_R$  are internal signals. To select either the left or right port, both  $\overline{CE}_0$  AND  $CE_1$  must be asserted to their active states ( $\overline{CE}_0 \leq V_{IL}$  and  $CE_1 \geq V_{IH}$ ).



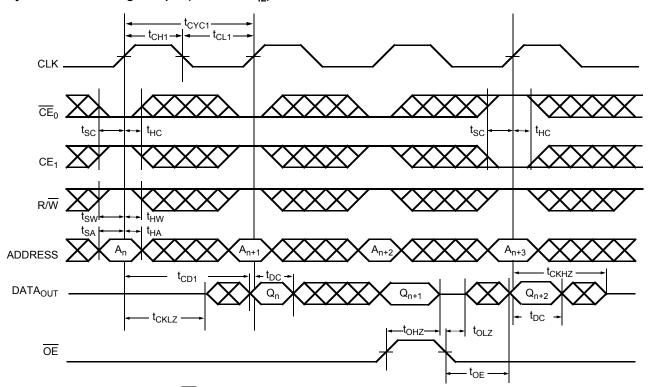
# $\label{eq:switching Characteristics} Switching Characteristics \mbox{ Over the Operating Range}$

		-9		-12			
Parameter	Description	Min.	Max.	Min.	Max.	Unit	
f <sub>MAX1</sub>	f <sub>Max</sub> Flow-Through		40		33	MHz	
f <sub>MAX2</sub>	f <sub>Max</sub> Pipelined		67		50	MHz	
t <sub>CYC1</sub>	Clock Cycle Time - Flow-Through	25		30		ns	
t <sub>CYC2</sub>	Clock Cycle Time - Pipelined	15		20		ns	
t <sub>CH1</sub>	Clock HIGH Time - Flow-Through	12		12		ns	
t <sub>CL1</sub>	Clock LOW Time - Flow-Through	12		12		ns	
t <sub>CH2</sub>	Clock HIGH Time - Pipelined	6		8		ns	
t <sub>CL2</sub>	Clock LOW Time - Pipelined	6		8		ns	
t <sub>R</sub>	Clock Rise Time		3		3	ns	
t <sub>F</sub>	Clock Fall Time		3		3	ns	
t <sub>SA</sub>	Address Set-up Time	4		4		ns	
t <sub>HA</sub>	Address Hold Time	1		1		ns	
t <sub>SC</sub>	Chip Enable Set-up Time	4		4		ns	
t <sub>HC</sub>	Chip Enable Hold Time	1		1		ns	
t <sub>SW</sub>	R/W Set-up Time	4		4		ns	
t <sub>HW</sub>	R/W Hold Time	1		1		ns	
t <sub>SD</sub>	Input Data Set-up Time	4		4		ns	
t <sub>HD</sub>	Input Data Hold Time	1		1		ns	
t <sub>SAD</sub>	ADS Set-up Time	4		4		ns	
t <sub>HAD</sub>	ADS Hold Time	1		1		ns	
t <sub>SCN</sub>	CNTEN Set-up Time	4		4		ns	
t <sub>HCN</sub>	CNTEN Hold Time	1		1		ns	
t <sub>SRST</sub>	CNTRST Set-up Time	4		4		ns	
t <sub>HRST</sub>	CNTRST Hold Time	1		1		ns	
t <sub>OE</sub>	Output Enable to Data Valid		10		12	ns	
t <sub>OLZ</sub>	OE to Low Z	2		2		ns	
t <sub>онz</sub>	OE to High Z	1	7	1	7	ns	
t <sub>CD1</sub>	Clock to Data Valid - Flow-Through		20		25	ns	
t <sub>CD2</sub>	Clock to Data Valid - Pipelined		9		12	ns	
t <sub>DC</sub>	Data Output Hold After Clock HIGH	2		2		ns	
t <sub>скнz</sub>	Clock HIGH to Output High Z	2	9	2	9	ns	
t <sub>CKLZ</sub>	Clock HIGH to Output Low Z	2		2		ns	
Port to Port	Delays	<b>I</b>		1			
CWDD	Write Port Clock High to Read Data Delay		40		40	ns	
t <sub>ccs</sub>	Clock to Clock Set-up Time		15		15	ns	

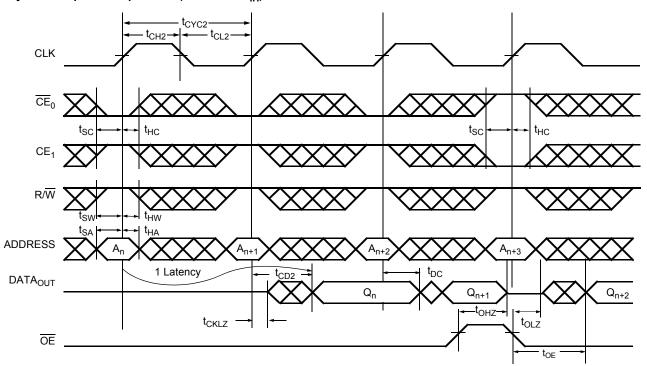


#### Switching Waveforms

Read Cycle for Flow-Through Output  $(\overline{FT}/PIPE = V_{IL})^{[7, 8, 9, 10]}$ 



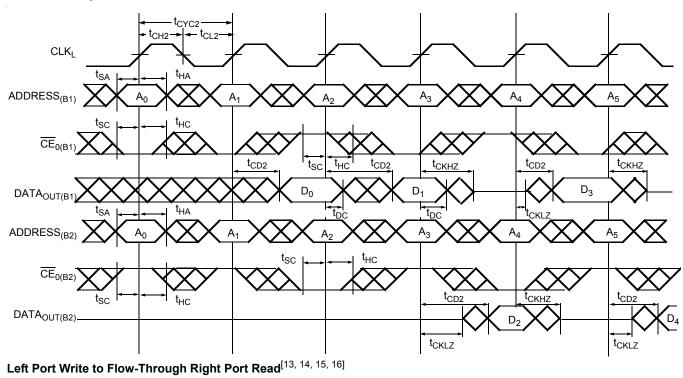
Read Cycle for Pipelined Operation ( $\overline{FT}$ /PIPE = V<sub>IH</sub>)<sup>[7, 8, 9, 10]</sup>

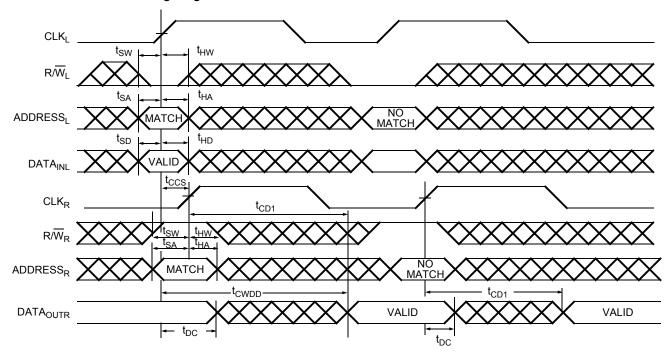


Notes:
OE is asynchronously controlled; all other inputs are synchronous to the rising clock edge.
ADS = V<sub>IL</sub>, CNTEN and CNTRST = V<sub>IH</sub>
The output is disabled (high-impedance state) by CE<sub>0</sub>=V<sub>IH</sub> or CE<sub>1</sub> = V<sub>IL</sub> following the next rising edge of the clock.
Addresses do not have to be accessed sequentially since ADS = V<sub>IL</sub> constantly loads the address on the rising edge of the CLK. Numbers are for reference only.



### Bank Select Pipelined Read<sup>[11, 12]</sup>

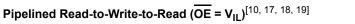


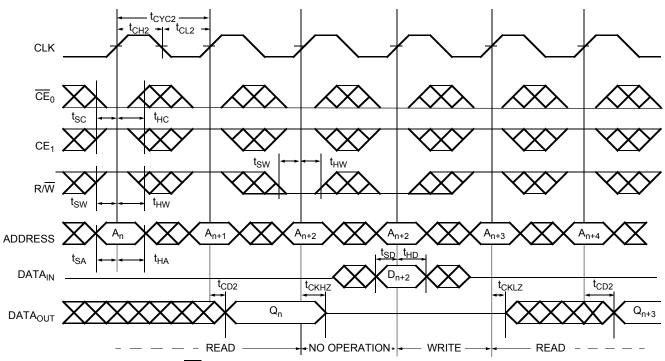


#### Notes:

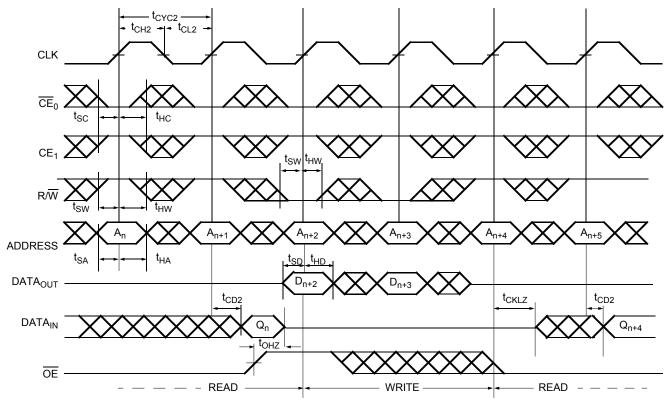
Notes:
11. In this depth expansion example, B1 represents Bank #1 and B2 is Bank #2; Each Bank consists of one Cypress dual-port device from this data sheet. ADDRESS<sub>(B1)</sub> = ADDRESS<sub>(B2)</sub>.
12. OE and ADS = V<sub>IL</sub>; CE<sub>1(B1)</sub>, CE<sub>1(B2)</sub>, RW, CNTEN, and CNTRST = V<sub>IH</sub>.
13. The same waveforms apply for a right port write to flow-through left port read.
14. <u>CE<sub>0</sub></u> and ADS = V<sub>IL</sub>; CE<sub>1</sub>, CNTEN, and CNTRST = V<sub>IH</sub>.
15. OE = V<sub>IL</sub>; or the right port, which is being read from. OE = V<sub>IH</sub> for the left port, which is being written to.
16. It t<sub>CCS</sub> ≤ maximum specified, then data from right port READ is not valid until the maximum specified for t<sub>CWDD</sub>. If t<sub>CCS</sub>>maximum specified, then data is not valid until t<sub>CCS</sub> + t<sub>CD1</sub>. t<sub>CWDD</sub> does not apply in this case.







Pipelined Read-to-Write-to-Read (OE Controlled)<sup>[10, 17, 18, 19]</sup>

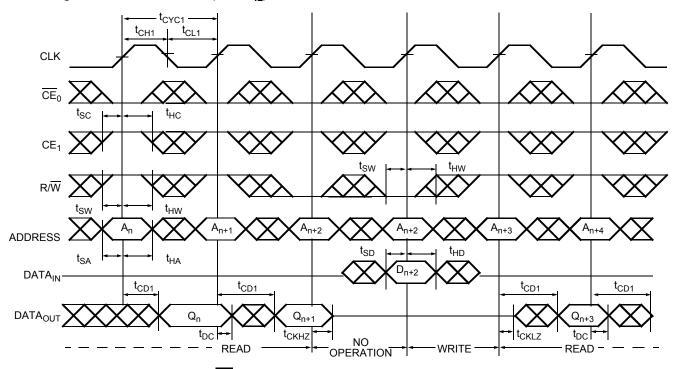


#### Notes:

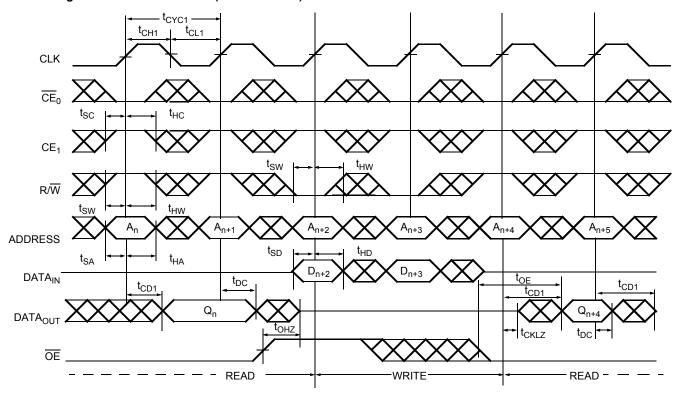
17. Output state (HIGH, LOW, or High-Impedance) is determined by the previous cycle control signals.
 18. CE<sub>0</sub> and ADS = V<sub>IL</sub>; CE<sub>1</sub>, CNTEN, and CNTRST = V<sub>IH</sub>.
 19. During "No operation," data in memory at the selected address may be corrupted and should be rewritten to ensure data integrity.



Flow-Through Read-to-Write-to-Read ( $\overline{OE} = V_{IL}$ )<sup>[8, 10, 17, 18, 19]</sup>

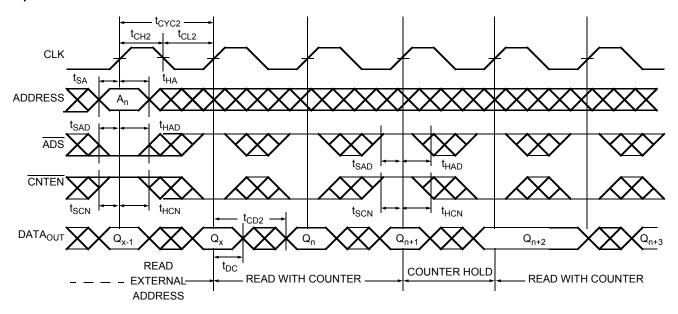


Flow-Through Read-to-Write-to-Read (OE Controlled)<sup>[8, 10, 17, 18, 19]</sup>

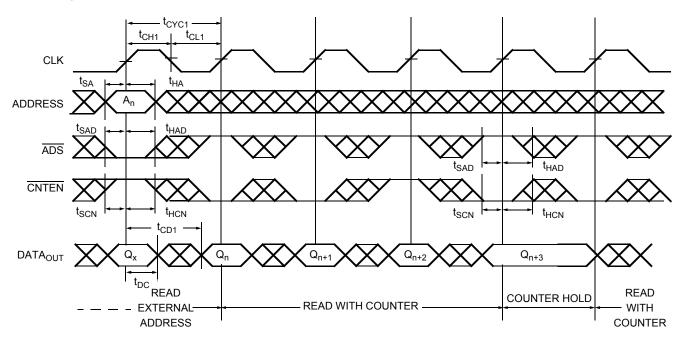




Pipelined Read with Address Counter Advance<sup>[20]</sup>



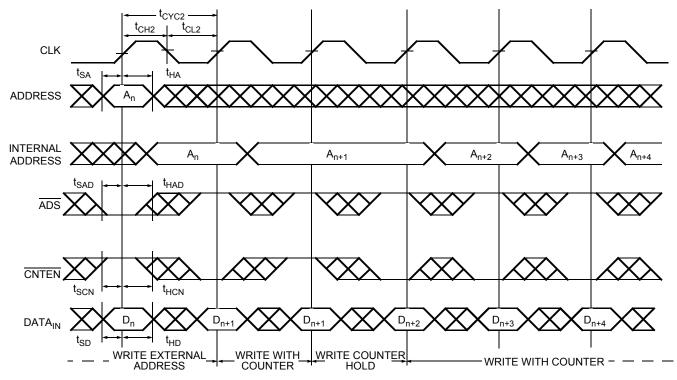
#### Flow-Through Read with Address Counter Advance<sup>[20]</sup>



Note: 20.  $\overline{CE}_0$  and  $\overline{OE}$  = V<sub>IL</sub>; CE<sub>1</sub>, R/W and  $\overline{CNTRST}$  = V<sub>IH</sub>.



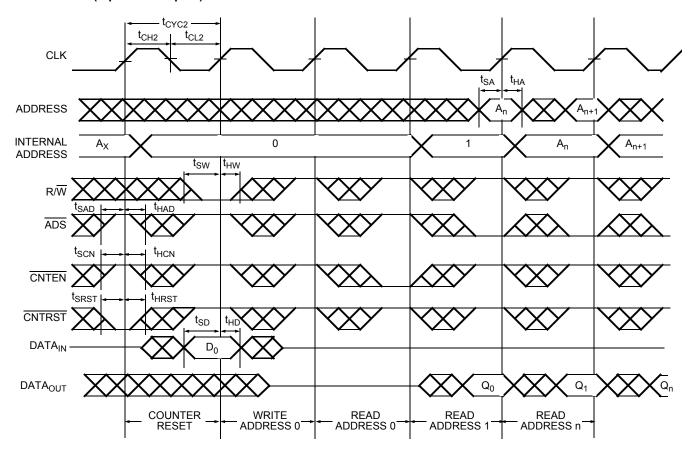
Write with Address Counter Advance (Flow-Through or Pipelined Outputs)<sup>[21, 22]</sup>



Notes: 21.  $\overline{CE_0}$  and  $\overline{R/W} = V_{IL}$ ;  $\overline{CE_1}$  and  $\overline{CNTRST} = V_{IH}$ . 22. The "Internal Address" is equal to the "External Address" when  $\overline{ADS} = V_{IL}$  and equals the counter output when  $\overline{ADS} = V_{IH}$ .



Counter Reset (Pipelined Outputs)<sup>[10, 17, 23, 24]</sup>



Notes: 23.  $CE_0 = V_{IL}$ ;  $CE_1 = V_{IH}$ . 24. No dead cycle exists during counter reset. A READ or WRITE cycle may be coincidental with the counter reset.



# Read/Write and Enable Operation<sup>[25, 26, 27]</sup>

Inputs Outputs						
OE	CLK	CE0	CE1	R/W	I/O <sub>0</sub> –I/O <sub>9</sub>	Operation
Х		Н	Х	Х	High-Z	Deselected <sup>[28]</sup>
Х		Х	L	Х	High-Z	Deselected <sup>[28]</sup>
Х		L	Н	L	D <sub>IN</sub>	Write
L		L	Н	Н	D <sub>OUT</sub>	Read <sup>[28]</sup>
Н	Х	L	Н	Х	High-Z	Outputs Disabled

# Address Counter Control Operation<sup>[25, 29, 30, 31]</sup>

Address	Previous Address	CLK	ADS	CNTEN	CNTRST	I/O	Mode	Operation
Х	Х	Γ	Х	Х	L	D <sub>out(0)</sub>	Reset	Counter Reset to Address 0
A <sub>n</sub>	Х	Γ	L	Х	Н	D <sub>out(n)</sub>	Load	Address Load into Counter
Х	A <sub>n</sub>		Н	Н	Н	D <sub>out(n)</sub>	Hold	External Address Blocked—Counter Disabled
Х	A <sub>n</sub>		Н	L	Н	D <sub>out(n+1)</sub>	Increment	Counter Enabled—Internal Address Generation

#### Notes:

**Notes:** 25. "X" = "don't care," "H" =  $V_{IH}$ , "L" =  $V_{IL}$ . 26. <u>ADS</u>, CNTEN, CNTRST = "don't care." 27. OE is an asynchronous input signal. 28. <u>When CE ch</u>anges state in the <u>pi</u>pelined mode, deselection and read happen in the following clock cycle. 29. CE<sub>0</sub> and  $\overrightarrow{OE} = V_{IL}$ ; CE<sub>1</sub> and R/W =  $V_{IH}$ . 30. Data shown for Flow-through mode; <u>pipelined mode output will be delayed by one cycle</u>. 31. Counter operation is independent of CE<sub>0</sub> and CE<sub>1</sub>.



### **Ordering Information**

#### 8K x9 3.3V Synchronous Dual-Port SRAM

Speed (ns)	Ordering Code	Package Name	Package Type	Operating Range
9	CY7C09159AV-9AC	A100	100-Pin Thin Quad Flat Pack	Commercial
	CY7C09159AV-9AXC	A100	100-Pin Pb-Free Thin Quad Flat Pack	
12	CY7C09159AV-12AC	A100	100-Pin Thin Quad Flat Pack	Commercial
	CY7C09159AV-12AXC	A100	100-Pin Pb-Free Thin Quad Flat Pack	

#### 16K x9 3.3V Synchronous Dual-Port SRAM

Speed (ns)	Ordering Code	Package Name	Package Type	Operating Range
9	CY7C09169AV-9AC	A100	100-Pin Thin Quad Flat Pack	Commercial
12	CY7C09169AV-12AC	A100	100-Pin Thin Quad Flat Pack	Commercial
	CY7C09169AV-12AXC	A100	100-Pin Pb-Free Thin Quad Flat Pack	
	CY7C09169AV-12AI	A100	100-Pin Thin Quad Flat Pack	Industrial
	CY7C09169AV-12AXI	A100	100-Pin Pb-Free Thin Quad Flat Pack	

#### **Package Diagram**

#### 100-Pin Pb-Free Thin Plastic Quad Flat Pack (TQFP) A100 16.00±0.25 SQ 14.00±0.05 SQ DIMENSIONS ARE IN MILLIMETERS, 100 76 ЯНАНАНАНАНАНАНАНАНАТ 75 0.22±0.05 ſ R 0.08 MIN. 0\* MIN. 0.20 MAX. ÷. STAND-OFF 0.05 MIN. 0.25 0.15 MAX GAUGE PLANE 199999 R 0.08 MIN ۵° \_\_\_. 0.20 MAX. E 0.50 0.20 MIN TYP 0.60±0.15 1.00 REF.-± 51 25 🗆 DETAILA 26 50 NDTE: PKG, CAN HAVE SEATING PLANE 12°±1' OR (8X) -1.60 MAX. $1.40 \pm 0.05$ TOP LEFT CORNER CHAMFER 4 CORNERS CHAMFER 0.08 51-85048-\*B 0.20 MAX. SEE DETAIL A

100-Pin Thin Plastic Quad Flat Pack (TQFP) A100

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#### Document #: 38-06053 Rev. \*B

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# **Document History Page**

Document Title: CY7C09159AV/CY7C09169AV 3.3V 8K/16K x 9 Synchronous Dual Port SRAM Document Number: 38-06053				
REV.	ECN NO.	lssue Date	Orig. of Change	Description of Change
**	110205	11/15/01	SZV	Change from Spec number: 38-00839 to 38-06053
*A	122303	12/27/02	RBI	Power up requirements added to Maximum Ratings Information
*В	393581	See ECN	YIM	Added Pb-Free Logo Added Pb-Free parts to ordering information: CY7C09159AV-9AXC, CY7C09159AV-12AXC, CY7C09169AV-12AXC, CY7C09169AV-12AXI